

## Application Data Sheet

### **Application Information**

Application Type::	Regular
Subject Matter::	Utility
Title::	A SEMICONDUCTOR DEVICE WITH AN IMPROVED GATE ELECTRODE PATTERN AND A METHOD OF MANUFACTURING THE SAME
Attorney Docket Number::	001701.00188
Request for Early Publication?::	NO
Request for Non-Publication?::	NO
Total Drawing Sheets::	11
Small Entity?::	NO
Secrecy Order in Parent Appl.?::	NO

### **Applicant Information**

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Hisato
Family Name::	Oyamatsu
City of Residence::	Yokohama-shi
Country of Residence::	Japan
Street of mailing address::	c/o Kabushiki Kaisha Toshiba 1-1 Shibaura, 1-chome
City of mailing address::	Yokohama-shi
State or Province of mailing address::	
Country of mailing address::	Japan
Postal or Zip Code of mailing address::	

**Correspondence Information**

Correspondence Customer Number:: 22907

**Representative Information**

Representative Customer Number:: 22907

**Domestic Priority Information**

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This Application	Divisional	09/418,035	10/14/99

**Foreign Priority Information**

Country::	Application number::	Filing Date::	Priority Claimed::
Japan	10-293901	10/15/98	Yes

**Assignee Information**

Assignee name:: Kabushiki Kaisha Toshiba

City of mailing address:: Kawasaki-shi

Country of mailing address:: Japan